

20 V, dual N-channel Trench MOSFET 28 June 2016

**Product data sheet** 

### 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low leakage current
- Leadless ultra small and ultra thin SMD plastic package: 1.1 × 1.0 × 0.37 mm
- Exposed drain pad for excellent thermal conduction
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance  $R_{DSon} = 470 \text{ m}\Omega$

### 3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per transistor							
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
V <sub>GS</sub>	gate-source voltage	-		-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	600	mA
Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 600 mA; T <sub>j</sub> = 25 °C		-	470	620	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	2 5	
4	S2	source TR2		
5	G2	gate TR2	3 4	
6	D1	drain TR1	Transparent top view	S1 S2 017aaa256
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

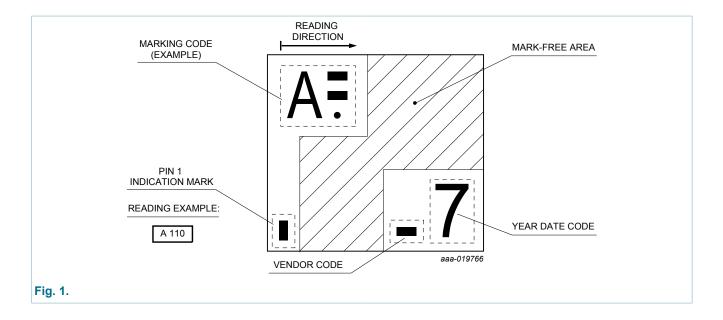
# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PMDXB600UNEL	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216			

# 7. Marking

Table 4. Marking codes	
Type number	Marking code
PMDXB600UNEL	C 001

#### 20 V, dual N-channel Trench MOSFET



### 8. Limiting values

#### Table 5.Limiting values

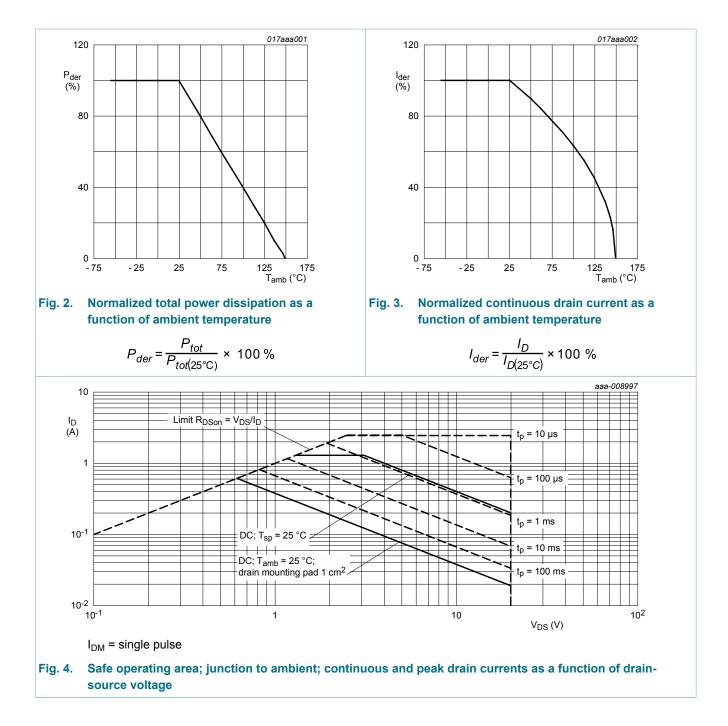
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	600	mA
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	400	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	2.5	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	265	m₩
			[1]	-	380	mW
		T <sub>sp</sub> = 25 °C		-	4025	mW
Per device			1		1	
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.4	А

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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### 9. Thermal characteristics

Table 6.     Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	410	475	K/W
from junction to ambient			[2]	-	285	330	K/W

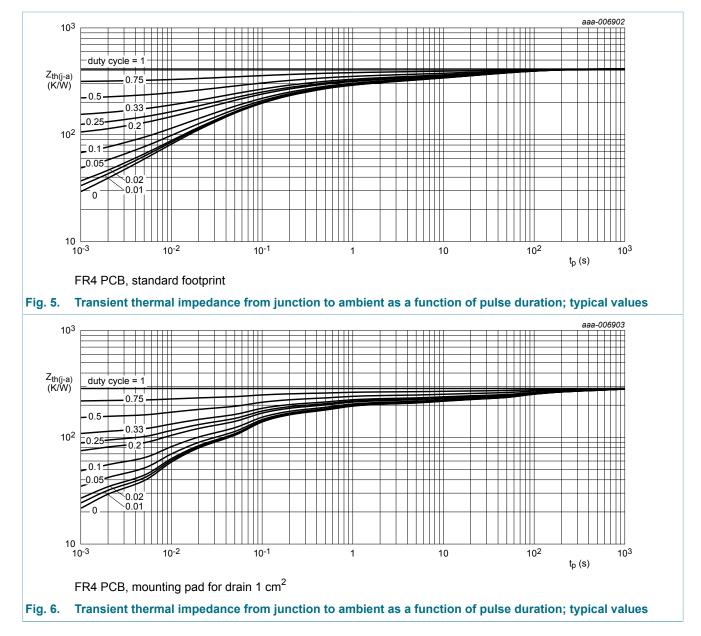
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



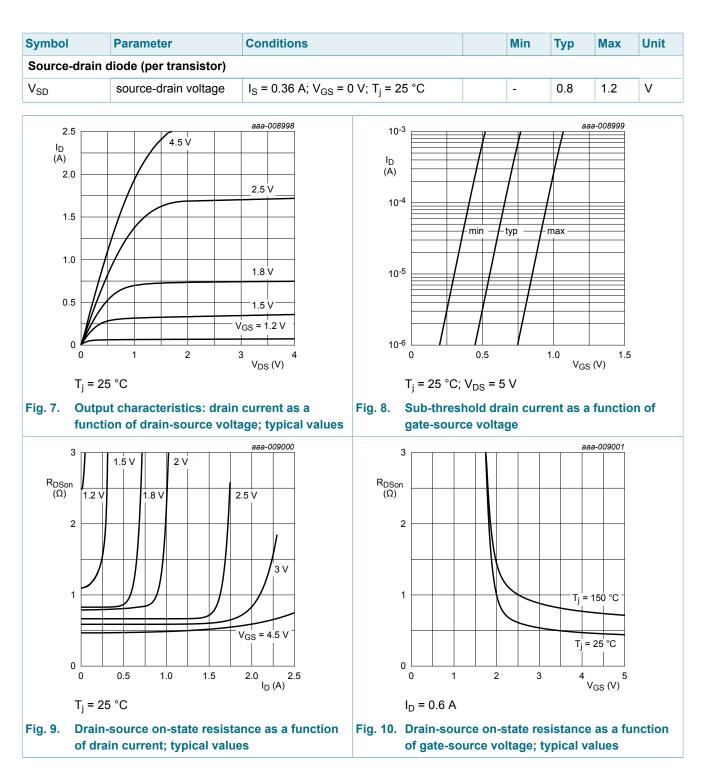
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	20	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	I <sub>D</sub> = 250 μA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	0.45	0.7	0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{DS}$ = 5 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	25	nA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	10	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 1.8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	50	nA
		V <sub>GS</sub> = -1.8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-50	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 600 mA; T <sub>j</sub> = 25 °C	-	470	620	mΩ
	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 600 mA; T <sub>j</sub> = 150 °C	-	760	1000	mΩ
		$V_{GS}$ = 2.5 V; I <sub>D</sub> = 500 mA; T <sub>j</sub> = 25 °C	-	620	850	mΩ
		$V_{GS}$ = 1.8 V; I <sub>D</sub> = 100 mA; T <sub>j</sub> = 25 °C	-	845	1300	mΩ
		$V_{GS}$ = 1.5 V; I <sub>D</sub> = 10 mA; T <sub>j</sub> = 25 °C	-	1125	3000	mΩ
		$V_{GS}$ = 1.2 V; I <sub>D</sub> = 1 mA; T <sub>j</sub> = 25 °C	-	2210	-	mΩ
9 <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 5 V; I <sub>D</sub> = 0.6 A; T <sub>j</sub> = 25 °C	-	1	-	S
Dynamic ch	naracteristics (per transist	or)	·			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 10 V; I <sub>D</sub> = 600 mA; V <sub>GS</sub> = 4.5 V;	-	0.4	0.7	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = 10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	21.3	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	5.4	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4.2	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; I <sub>D</sub> = 600 mA; V <sub>GS</sub> = 4.5 V;	-	5.6	-	ns
t <sub>r</sub>	rise time	R <sub>G(ext)</sub> = 6 Ω; T <sub>j</sub> = 25 °C	-	9.2	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	51	-	ns

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## PMDXB600UNEL

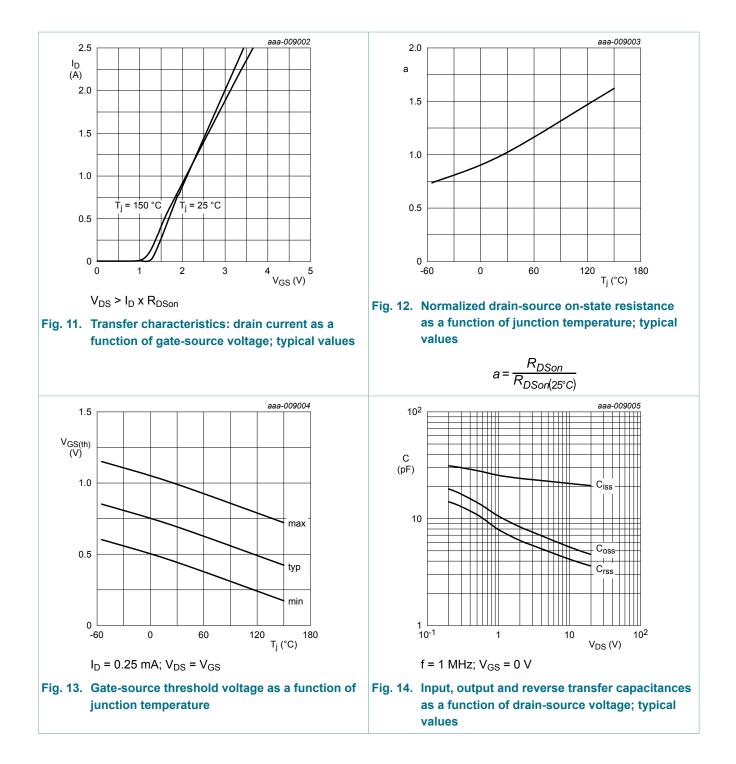
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# **PMDXB600UNEL**

#### 20 V, dual N-channel Trench MOSFET

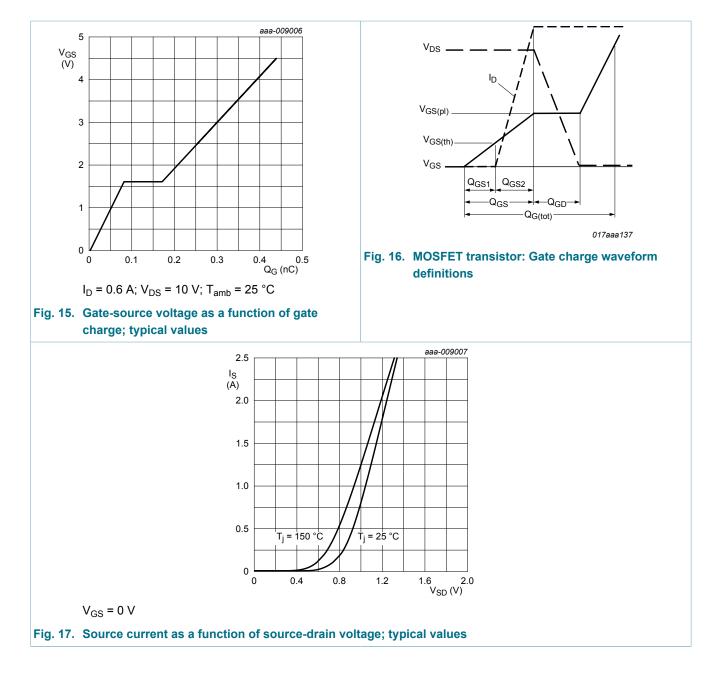


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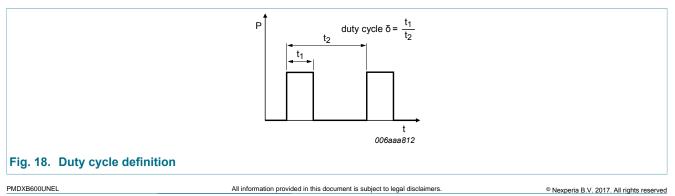
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# **PMDXB600UNEL**

#### 20 V, dual N-channel Trench MOSFET

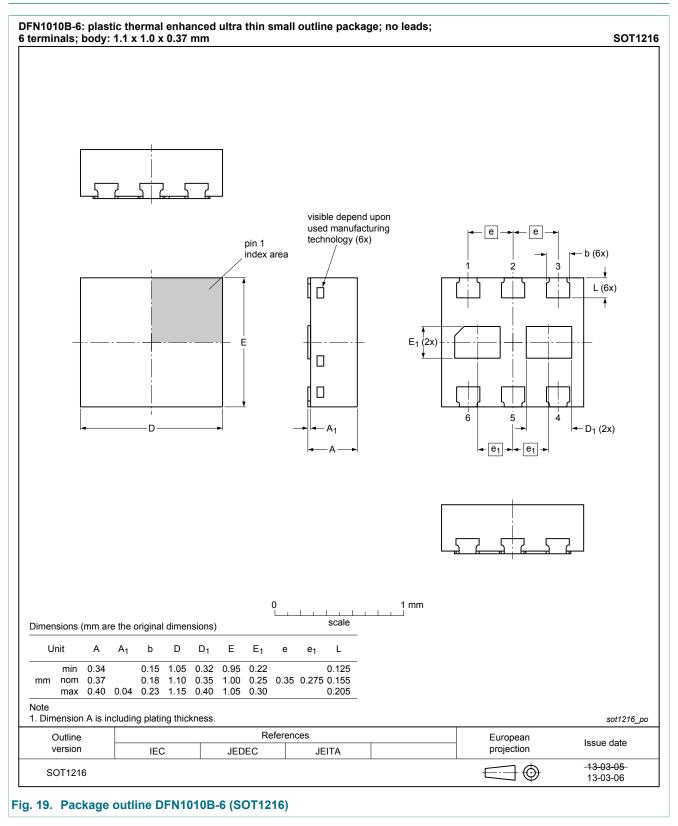


# **11. Test information**



#### 20 V, dual N-channel Trench MOSFET

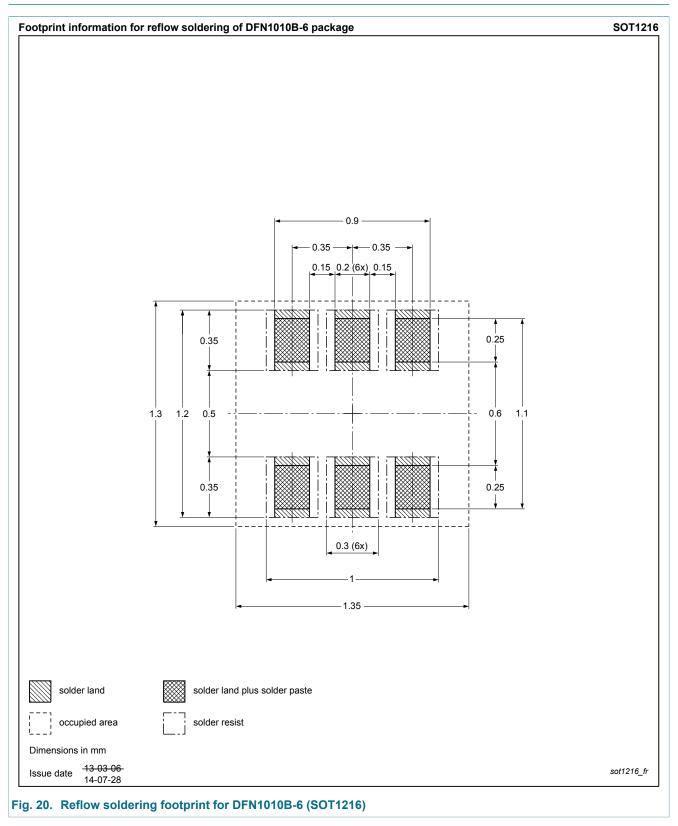
### 12. Package outline



PMDXB600UNEL

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### 13. Soldering



# 14. Revision history

Table 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes	
PMDXB600UNEL v.1	20160628	Product data sheet	-	-	

#### 20 V, dual N-channel Trench MOSFET

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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